SCES060B - DECEMBER 1995 - REVISED FEBRUARY 1999

- Member of the Texas Instruments Widebus™ Family
- EPIC[™] (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 18-bit bus transceiver is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVCH16863 is an 18-bit noninverting transceiver designed for synchronous communication between data buses. The control-function implementation minimizes external timing requirements.

The SN74ALVCH16863 can be used as two 9-bit transceivers or one 18-bit transceiver. They allow data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the output-enable (OEAB or OEBA) inputs.

DGG OR DL PACKAGE (TOP VIEW)

				1
10EAB	1	\cup	56	1 <mark>OEBA</mark>
1B1 [2		55]1A1
1B2 🕻	3		54]1A2
GND [4		53	GND
1B3 [5		52	1A3
1B4 🛚	6		51]1A4
v _{cc} [7		50	
1B5 🛚	8			1A5
1B6 🛚	9			1A6
1B7 🛚	10] 1A7
GND	11			GND
1B8 🛚	12			1A8
1B9 🛚	13		44	1A9
GND [14			GND
GND [15			GND
2B1 🛚	16		41	
2B2 🛚	17			2A2
GND [18			GND
2B3	19			2A3
2B4 🛚	20		37	
2B5 🛚	21			2A5
v _{cc} [22		35	$[v_{cc}]$
2B6 🛚	23		34	2A6
2B7 🛚	24		33	2A7
GND [25		32	
2B8 🛚	26		31	2A8
2B9 [27		30	2 <u>A</u> 9
2OEAB	28		29	2 <mark>OEBA</mark>
'				-

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16863 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE (each 9-bit section)

INP	UTS	ODEDATION				
OEAB	OEBA	OPERATION				
Н	L	B data to A bus				
L	Н	A data to B bus				
Н	Н	Isolation				

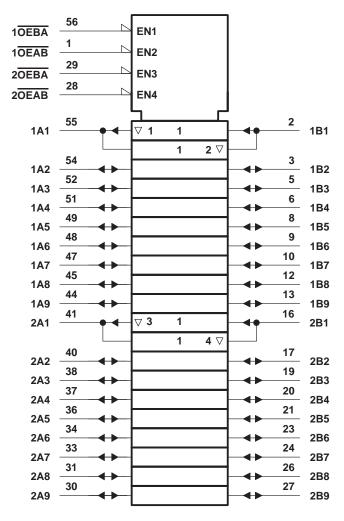


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

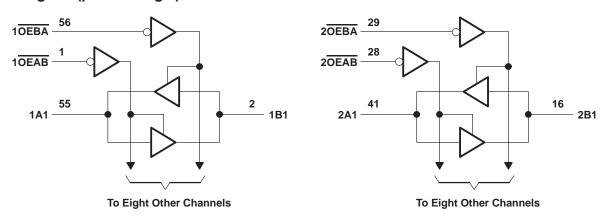


logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





SCES060B - DECEMBER 1995 - REVISED FEBRUARY 1999

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Sup	oply voltage range, V _{CC}	
Inpu	ut voltage range, V _I : Except I/O ports (see Note 1)	
	I/O ports (see Notes 1 and 2)	\dots -0.5 V to V _{CC} + 0.5 V
Out	tput voltage range, V _O (see Notes 1 and 2)	\dots -0.5 V to V _{CC} + 0.5 V
Inpu	ut clamp current, I _{IK} (V _I < 0)	–50 mA
Out	tput clamp current, I _{OK} (V _O < 0)	–50 mA
Con	ntinuous output current, IO	±50 mA
Con	ntinuous current through each V _{CC} or GND	±100 mA
Pac	ckage thermal impedance, θ _{JA} (see Note 3): DGG packag	le 81°C/W
	DL package	
Stor	rage temperature range, T _{stg}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 4.6 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
Vcc	Supply voltage		1.65	3.6	V
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}		
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		0.35 × V _{CC}	
V_{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	
VI	Input voltage		0	VCC	V
٧o	Output voltage		0	VCC	V
		V _{CC} = 1.65 V		-4	mA
1	Lligh lovel output ourrent	V _{CC} = 2.3 V		-12	
ЮН	High-level output current	V _{CC} = 2.7 V		-12	IIIA
		V _{CC} = 3 V		-24	
		V _{CC} = 1.65 V		4	
1	Lavidaval autaut aussat	V _{CC} = 2.3 V		12	4
IOL	Low-level output current	V _{CC} = 2.7 V		12	mA
	V _{CC} = 3 V			24	
Δt/Δν	Input transition rise or fall rate	·		10	ns/V
TA	Operating free-air temperature		-40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST CO	ONDITIONS	Vcc	MIN	TYP [†]	MAX	UNIT	
		I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	.2			
		I _{OH} = -4 mA		1.65 V	1.2				
		I _{OH} = -6 mA		2.3 V	2				
Vон				2.3 V	1.7			V	
		I _{OH} = -12 mA		2.7 V	2.2				
				3 V	2.4				
		I _{OH} = -24 mA		3 V	2				
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2		
		I _{OL} = 4 mA		1.65 V			0.45		
		I _{OL} = 6 mA		2.3 V			0.4	V	
VOL		104		2.3 V			0.7	V	
		I _{OL} = 12 mA		2.7 V			0.4		
		I _{OL} = 24 mA		3 V			0.55		
lį		V _I = V _{CC} or GND		3.6 V			±5	μΑ	
		V _I = 0.58 V	1.65 V	25					
		V _I = 1.07 V		1.65 V	-25				
		V _I = 0.7 V		2.3 V	45				
I _I (hold)		V _I = 1.7 V		2.3 V	-45			μΑ	
		V _I = 0.8 V		3 V	75				
		V _I = 2 V		3 V	-75				
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$		3.6 V			±500		
loz		VO = VCC or GND		3.6 V			±10	μΑ	
Icc		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40	μΑ	
ΔlCC		One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	3 V to 3.6 V			750	μΑ	
Ci	Control inputs Data inputs	V _I = V _{CC} or GND		3.3 V		3.5 6		pF	
Co	Outputs	V _O = V _{CC} or GND		3.3 V		7.5		pF	

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V	V _{CC} = ± 0.2	2.5 V 2 V	V _{CC} =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
		(0011-01)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	B or A	§	1	4.1		4	1	3.4	ns
t _{en}	OEAB or OEBA	A or B	§	1	5.7		5.8	1	4.7	ns
^t dis	OEAB or OEBA	A or B	§	1.3	5.5		4.7	1.4	4.2	ns

[§] This information was not available at the time of publication.



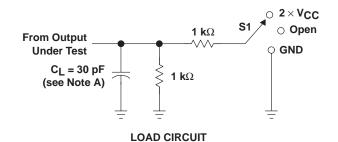
[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. ‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

operating characteristics, T_A = 25°C

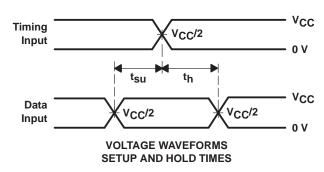
PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT	
	FARAMETER			TYP	ן וואוט		
	Power dissipation Outputs enabled		C. F0.5F & 40.MU	†		30	pF
Cpd	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	2	3	рг

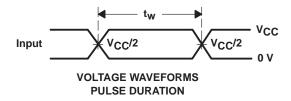
[†] This information was not available at the time of publication.

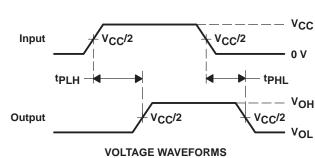
PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.8 V



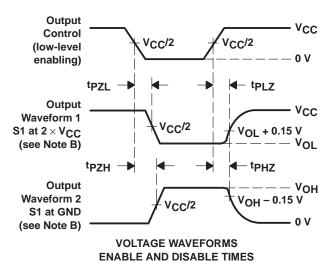








PROPAGATION DELAY TIMES



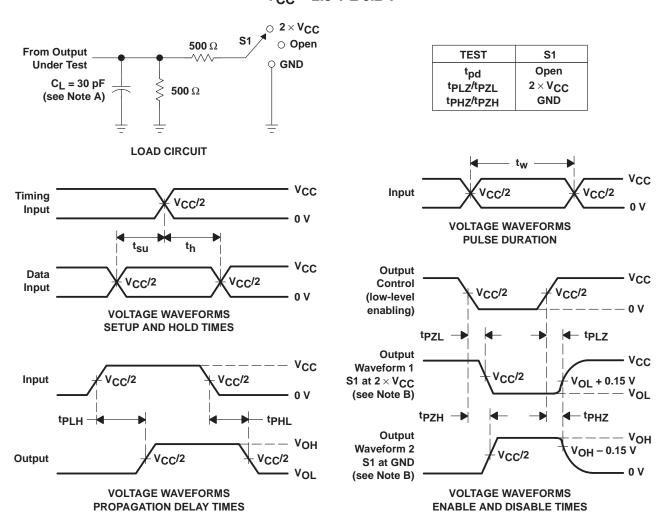
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.5 V \pm 0.2 V



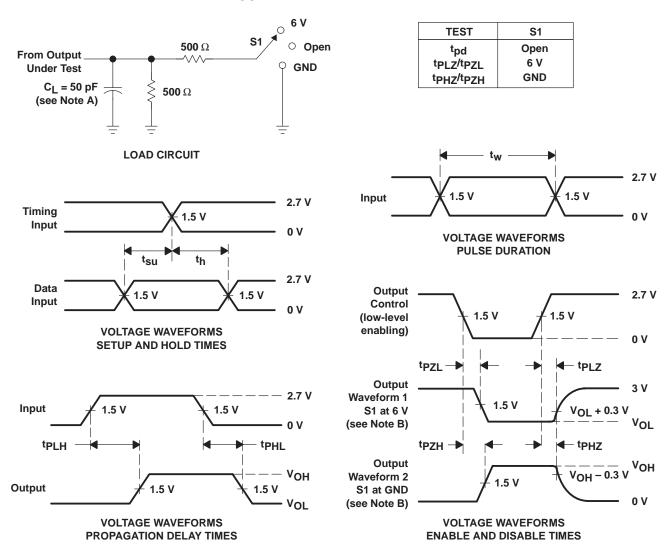
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2$ ns. $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated